Zibo Seno Electronic Engineering Co., Ltd.



MBRF1040CT - MBRF10200CT





10.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

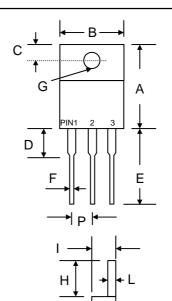
Case: ITO-220AB, Molded Plastic

Terminals: Plated Leads Solderable per

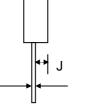
MIL-STD-202, Method 208

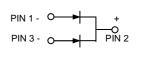
Polarity: See DiagramMounting Position: Any

Lead Free: For RoHS / Lead Free Version



ITO-220AB								
Dim	Min	Max						
Α	14.50	15.50						
В	9.50	10.50						
C	2.55	2.90						
D	3.30	4.30						
Е	13.00	14.00						
F	0.30	0.90						
G	3.00 Ø	3.80 Ø						
H	6.30	7.30						
ı	4.20	4.80						
7	2.50	2.90						
K	0.47	0.75						
L	2.50	3.10						
Р	2.35	2.75						
All Dimensions in mm								





Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBRF 1040 CT	MBRF 1045 CT	MBRF 1050 CT	MBRF 1060 CT	MBRF 10100 CT	MBRF 10150 CT	MBRF 10200 CT	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	40	45	50	60	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	70	105	140	V
Average Rectified Output Current @T _L = 75°C (Note 1)	lo	10.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	100					110		А
Forward Voltage @I _F = 5A	VFM	0.70		0.80		0.85		0.92	V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	lгм	0.1 20						mA	
Typical Junction Capacitance (Note 2)	Cj	350		280		200		pF	
Typical Thermal Resistance (Note 1)	R_{θ} JA	3.0 2.0					°C/W		
Operating and Storage Temperature Range	Tj, Tstg	-55 to +150 -55 to +175					+175	°C	

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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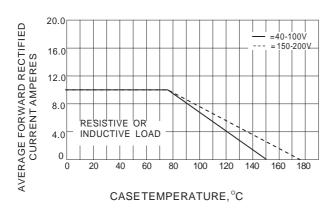


Fig.1 - FORWARD CURRENT DERATING CURVE

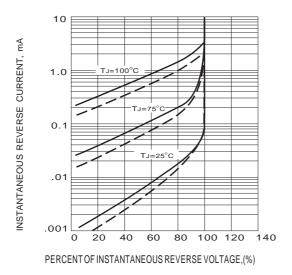


Fig.3 - TYPICAL REVERSE CHARACTERISTICS

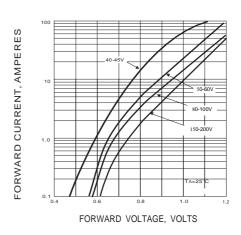


Fig.2 - TYPICAL INSTANTANEOUS FORWAR CHARACTERISTIC

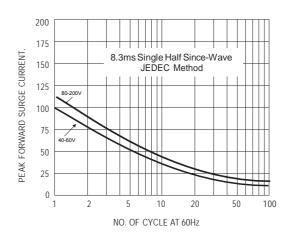


Fig.4 - TYPICAL INSTANTANEOUS FORWARD **CHARACTERISTICS**